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Andreas Erdmann, Fraunhofer Institute for Integrated Systems and Device Technology (Germany)
Nigel R. Farrar, Cymer, Inc. (United States)
Carlos Fonseca, Tokyo Electron America, Inc. (United States)
Tsai-Sheng Gau, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
Bernd Geh, Carl Zeiss SMT Inc./ASML TDC (United States)
Yuri Granik, Mentor Graphics Corporation (United States)
Soichi Inoue, EUVL Infrastructure Development Center, Inc. (Japan)
Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)
Suk Joo Lee, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)
Wilhelm Maurer, Infineon Technologies AG (Germany)
Soichi Owa, Nikon Corporation (Japan)
Xuelong Shi, Semiconductor Manufacturing International Corporation (China)
Sam Sivakumar, Intel Corporation (United States)
Bruce W. Smith, Rochester Institute of Technology (United States)
Kazuhiro Takahashi, Canon Inc. (Japan)
Geert Vandenberghe, IMEC (Belgium)
Session Chairs

1 Overlay Topics in Advanced Optical Microlithography: Joint Session with Conference 8324
   Bernd Geh, Carl Zeiss SMT Inc./ASML TDC (United States)
   Will Conley, Dynamic Intelligence (United States)

2 Invited Session
   Will Conley, Dynamic Intelligence (United States)
   Kafai Lai, IBM Corporation (United States)

3 SMO-Modeling
   Andreas Erdmann, Fraunhofer Institute for Integrated Systems and Device Technology (Germany)
   Nigel R. Farrar, Cymer, Inc. (United States)

4 Multiple Patterning I
   Peter D. Brooker, Synopsys, Inc. (United States)
   Will Conley, Dynamic Intelligence (United States)

5 Source and Mask Optimization
   Carlos Fonseca, Tokyo Electron America, Inc. (United States)
   Will Conley, Dynamic Intelligence (United States)

6 Tools and Process Control I
   Yuri Granik, Mentor Graphics Corporation (United States)
   Soichi Inoue, EUVL Infrastructure Development Center, Inc. (Japan)

7 Lithography at the Intersection of Optics and Chemistry: Joint Session with Conference 8325
   Mark H. Somervell, Tokyo Electron America, Inc. (United States)
   Will Conley, Dynamic Intelligence (United States)

8 Tools and Process Control II
   Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)
   Wilhelm Maurer, Infineon Technologies AG (Germany)

9 Multiple Patterning/Innovative Lithography
   Sam Sivakumar, Intel Corporation (United States)
   Peter D. Brooker, Synopsys, Inc. (United States)
   Pary Baluswamy, Micron Technology, Inc. (United States)

10 Optical/DFM: Joint Session with Conference 8327
    Will Conley, Dynamic Intelligence (United States)
    Mark E. Mason, Texas Instruments Inc. (United States)
Joint Session with Conference 8327
John L. Sturtevant, Mentor Graphics Corporation (United States)
Kafai Lai, IBM Corporation (United States)

OPC
Bruce W. Smith, Rochester Institute of Technology (United States)
Kazuhiro Takahashi, Canon Inc. (Japan)

Tools
Soichi Owa, Nikon Corporation (Japan)
Kafai Lai, IBM Corporation (United States)

Poster Session
Peter D. Buck, Toppan Photomasks, Inc. (United States)
Geert Vandenberghe, IMEC (Belgium)